# FAIRCHILD

SEMICONDUCTOR

# **KSC900**

## Low Frequency & Low Noise Amplifier

- Collector-Base Voltage : V<sub>CBO</sub>=30V
  Low Noise Level : NL=50mV (MAX)
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



## **NPN Epitaxial Silicon Transistor**

## Absolute Maximum Ratings T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V <sub>CBO</sub>	Collector-Base Voltage	30	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	25	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
I <sub>C</sub>	Collector Current	50	mA	
P <sub>C</sub>	Collector Power Dissipation	250	mW	
TJ	Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C	

## Electrical Characteristics Ta=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =100μA, I <sub>E</sub> =0	30			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0	25			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =10μΑ, I <sub>C</sub> =0	5			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =25V, I <sub>E</sub> =0			50	nA
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> =3V, I <sub>C</sub> =0			100	nA
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =3V, I <sub>C</sub> =0.5mA	120		1000	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =20mA, I <sub>B</sub> =2mA		0.1	0.2	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> =3V, I <sub>C</sub> =0.5mA		0.62	0.7	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =3V, I <sub>C</sub> =1mA		100		MHz
NL	Noise Level	$V_{CC}$ =12V, I <sub>C</sub> =0.1mA R <sub>S</sub> =25k $\Omega$ A <sub>V</sub> =80dB, f=1KHz		30	50	mV

## h<sub>FE</sub> Classification

Classification	Y	G	L	V
h <sub>FE</sub>	120 ~ 240	200 ~ 400	350 ~ 700	600 ~ 1000

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Programmable Ac	tive Droop™	OPTOPLANAR™	SMART START™	

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